



# RF Power LDMOS Transistors

## High Ruggedness N-Channel Enhancement-Mode Lateral MOSFETs

These high ruggedness devices are designed for use in high VSWR industrial, medical, broadcast, aerospace and mobile radio applications. Their unmatched input and output design supports frequency use from 1.8 to 400 MHz.

### Typical Performance

Frequency (MHz)	Signal Type	V <sub>DD</sub> (V)	P <sub>out</sub> (W)	G <sub>ps</sub> (dB)	η <sub>D</sub> (%)
87.5–108 (1,2)	CW	62	680 CW	21.3	83.0
230 (3)	Pulse (100 μsec, 20% Duty Cycle)	65	600 Peak	26.4	74.4

### Load Mismatch/Ruggedness

Frequency (MHz)	Signal Type	VSWR	P <sub>in</sub> (W)	Test Voltage	Result
230 (3)	Pulse (100 μsec, 20% Duty Cycle)	> 65:1 at all Phase Angles	2.5 Peak (3 dB Overdrive)	65	No Device Degradation

1. Measured in 87.5–108 MHz broadband reference circuit (page 5).
2. The values shown are the center band performance numbers across the indicated frequency range.
3. Measured in 230 MHz production test fixture (page 10).

### Features

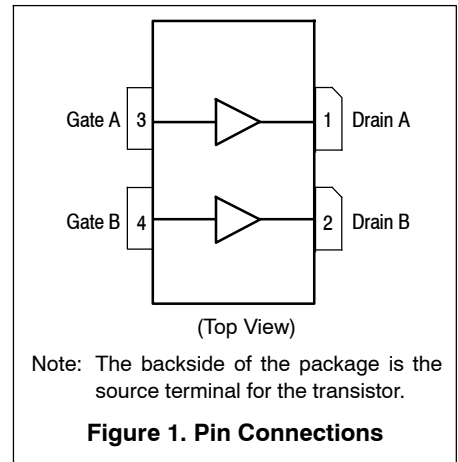
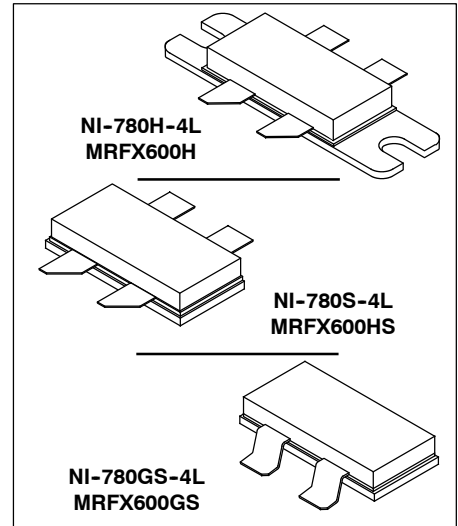
- Unmatched input and output allowing wide frequency range utilization
- Output impedance fits a 4:1 transformer
- Device can be used single-ended or in a push-pull configuration
- Qualified up to a maximum of 65 V<sub>DD</sub> operation
- Characterized from 30 to 65 V for extended power range
- High breakdown voltage for enhanced reliability
- Suitable for linear application with appropriate biasing
- Integrated ESD protection with greater negative gate-source voltage range for improved Class C operation
- Included in NXP product longevity program with assured supply for a minimum of 15 years after launch

### Typical Applications

- Industrial, scientific, medical (ISM)
  - Laser generation
  - Plasma generation
  - Particle accelerators
  - MRI, RF ablation and skin treatment
  - Industrial heating, welding and drying systems
- Radio and VHF TV broadcast
- Aerospace
  - HF communications
  - Radar
- Mobile radio
  - HF and VHF communications
  - PMR base stations

**MRFX600H**  
**MRFX600HS**  
**MRFX600GS**

**1.8–400 MHz, 600 W CW, 65 V  
WIDEBAND  
RF POWER LDMOS TRANSISTORS**



**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-0.5, +179	Vdc
Gate-Source Voltage	$V_{GS}$	-6.0, +10	Vdc
Storage Temperature Range	$T_{stg}$	-65 to +150	°C
Case Operating Temperature Range	$T_C$	-40 to +150	°C
Operating Junction Temperature Range (1,2)	$T_J$	-40 to +225	°C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	$P_D$	1333 6.67	W W/°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case CW: Case Temperature 75°C, 650 W CW, 62 Vdc, $I_{DQ(A+B)} = 250$ mA, 98 MHz	$R_{\theta JC}$	0.15	°C/W
Thermal Impedance, Junction to Case Pulse: Case Temperature 73°C, 600 W Peak, 100 $\mu\text{sec}$ Pulse Width, 20% Duty Cycle, 65 Vdc, $I_{DQ(A+B)} = 100$ mA, 230 MHz	$Z_{\theta JC}$	0.037	°C/W

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JS-001-2017)	Class 2, passes 2500 V
Charge Device Model (per JS-002-2014)	Class C3, passes 1000 V

**Table 4. Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**Off Characteristics (4)**

Gate-Source Leakage Current ( $V_{GS} = 5$ Vdc, $V_{DS} = 0$ Vdc)	$I_{GSS}$	—	—	1	$\mu\text{Adc}$
Drain-Source Breakdown Voltage ( $V_{GS} = 0$ Vdc, $I_D = 100$ mAdc)	$V_{(BR)DSS}$	179	193	—	Vdc
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 65$ Vdc, $V_{GS} = 0$ Vdc)	$I_{DSS}$	—	—	10	$\mu\text{Adc}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 179$ Vdc, $V_{GS} = 0$ Vdc)	$I_{DSS}$	—	—	100	$\mu\text{Adc}$

**On Characteristics**

Gate Threshold Voltage (4) ( $V_{DS} = 10$ Vdc, $I_D = 277$ $\mu\text{Adc}$ )	$V_{GS(th)}$	2.1	2.5	2.9	Vdc
Gate Quiescent Voltage ( $V_{DD} = 65$ Vdc, $I_D = 100$ mAdc, Measured in Functional Test)	$V_{GS(Q)}$	2.7	2.9	3.2	Vdc
Drain-Source On-Voltage (4) ( $V_{GS} = 10$ Vdc, $I_D = 0.74$ Adc)	$V_{DS(on)}$	—	0.2	—	Vdc
Forward Transconductance (4) ( $V_{DS} = 10$ Vdc, $I_D = 32$ Adc)	$g_{fs}$	—	33.6	—	S

1. Continuous use at maximum temperature will affect MTF.
2. MTF calculator available at <http://www.nxp.com/RF/calculators>.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.nxp.com/RF> and search for AN1955.
4. Each side of device measured separately.

(continued)

**Table 4. Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Dynamic Characteristics</b> <sup>(1)</sup>					
Reverse Transfer Capacitance ( $V_{DS} = 65\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{rss}$	—	1.1	—	pF
Output Capacitance ( $V_{DS} = 65\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{oss}$	—	84	—	pF
Input Capacitance ( $V_{DS} = 65\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz)	$C_{iss}$	—	299	—	pF

**Functional Tests** <sup>(2)</sup> (In NXP Production Test Fixture, 50 ohm system)  $V_{DD} = 65\text{ Vdc}$ ,  $I_{DQ(A+B)} = 100\text{ mA}$ ,  $P_{out} = 600\text{ W Peak}$  (120 W Avg.),  $f = 230\text{ MHz}$ , 100  $\mu\text{sec}$  Pulse Width, 20% Duty Cycle

Power Gain	$G_{ps}$	24.5	26.4	27.5	dB
Drain Efficiency	$\eta_D$	71.0	74.4	—	%
Input Return Loss	IRL	—	-23	-12	dB

**Table 5. Load Mismatch/Ruggedness** (In NXP Production Test Fixture, 50 ohm system)  $I_{DQ(A+B)} = 100\text{ mA}$ 

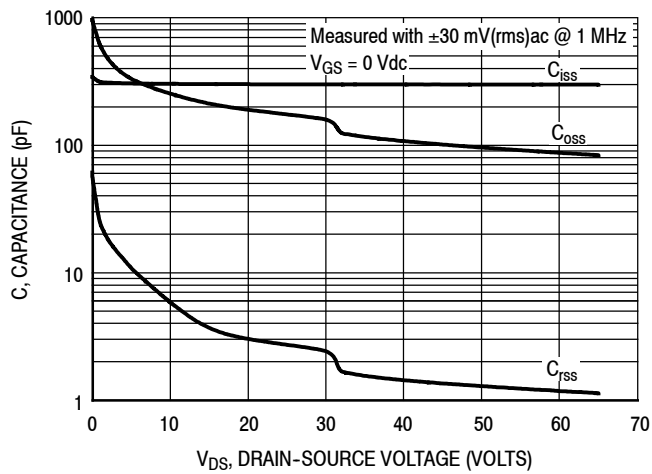
Frequency (MHz)	Signal Type	VSWR	$P_{in}$ (W)	Test Voltage, $V_{DD}$	Result
230	Pulse (100 $\mu\text{sec}$ , 20% Duty Cycle)	> 65:1 at all Phase Angles	2.5 Peak (3 dB Overdrive)	65	No Device Degradation

**Table 6. Ordering Information**

Device	Tape and Reel Information	Package
MRFX600HR5	R5 Suffix = 50 Units, 56 mm Tape Width, 13-inch Reel	NI-780H-4L
MRFX600HSR5	R5 Suffix = 50 Units, 32 mm Tape Width, 13-inch Reel	NI-780S-4L
MRFX600GSR5		NI-780GS-4L

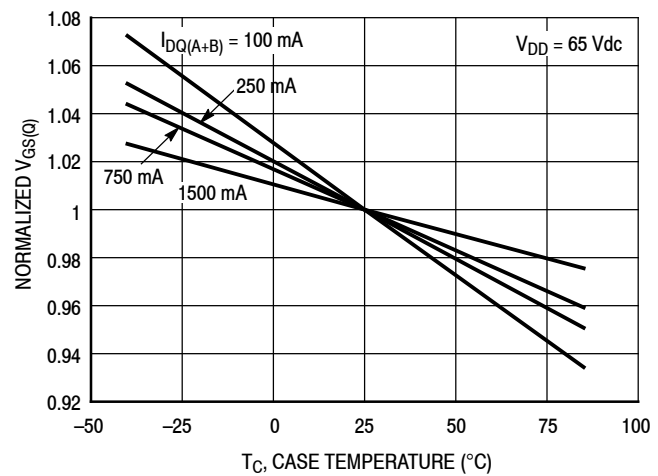
- Each side of device measured separately.
- Measurements made with device in straight lead configuration before any lead forming operation is applied. Lead forming is used for gull wing (GS) parts.

## TYPICAL CHARACTERISTICS



**Note:** Each side of device measured separately.

**Figure 2. Capacitance versus Drain-Source Voltage**



$I_{DQ}$ (mA)	Slope (mV/°C)
100	-3.20
250	-2.48
750	-2.16
1500	-1.36

**Figure 3. Normalized  $V_{GS}$  versus Quiescent Current and Case Temperature**

## 87.5–108 MHz BROADBAND REFERENCE CIRCUIT – 2.9" × 4.7" (7.3 cm × 12.0 cm)

**Table 7. 87.5–108 MHz Broadband Performance** (In NXP Reference Circuit, 50 ohm system)

$I_{DQ(A+B)} = 250$  mA,  $P_{in} = 5$  W, CW

Frequency (MHz)	$V_{DD}$ (V)	$P_{out}$ (W)	$G_{ps}$ (dB)	$\eta_D$ (%)
87.5	62	705	21.5	80.0
98	62	680	21.3	83.0
108	62	650	21.2	82.5

## 87.5–108 MHz BROADBAND REFERENCE CIRCUIT — 2.9" × 4.7" (7.3 cm × 12 cm)

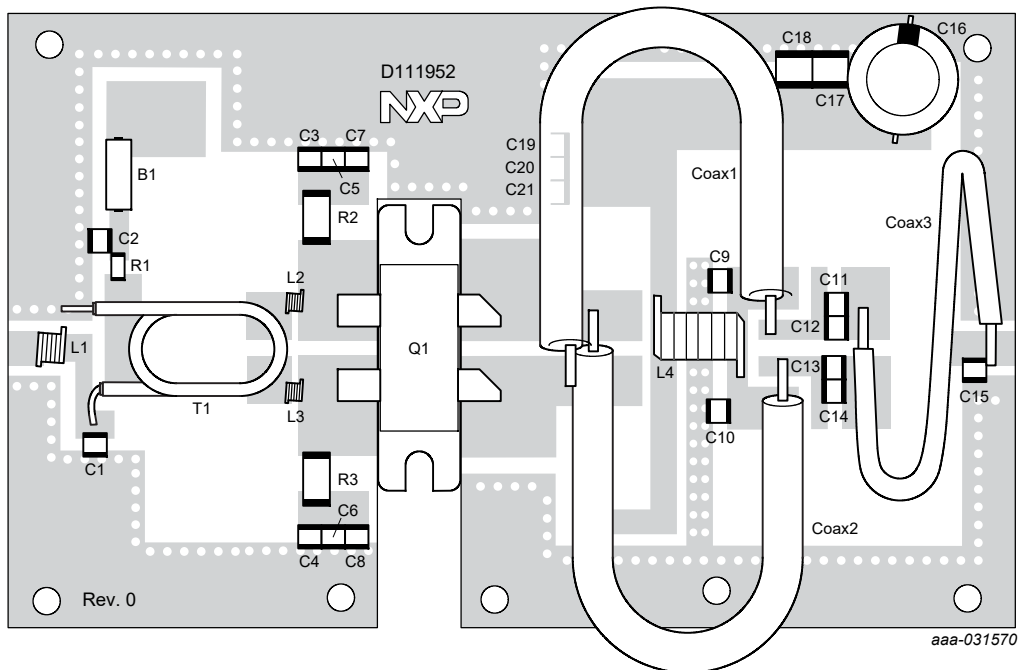


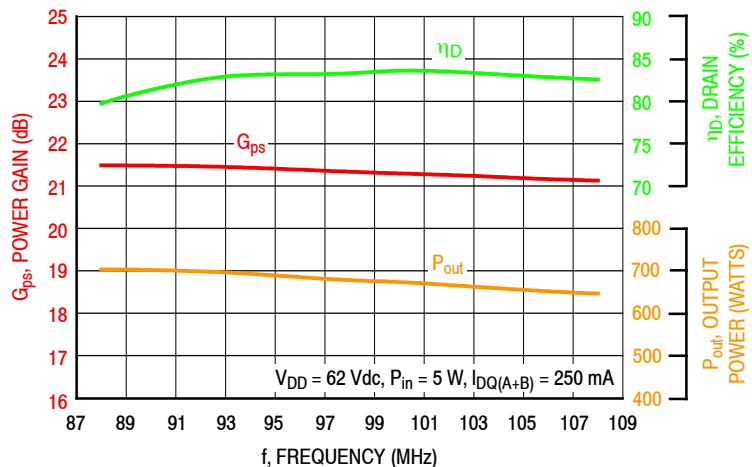
Figure 4. MRFX600H 87.5–108 MHz Broadband Reference Circuit Component Layout

Table 8. MRFX600H 87.5–108 MHz Broadband Reference Circuit Component Designations and Values

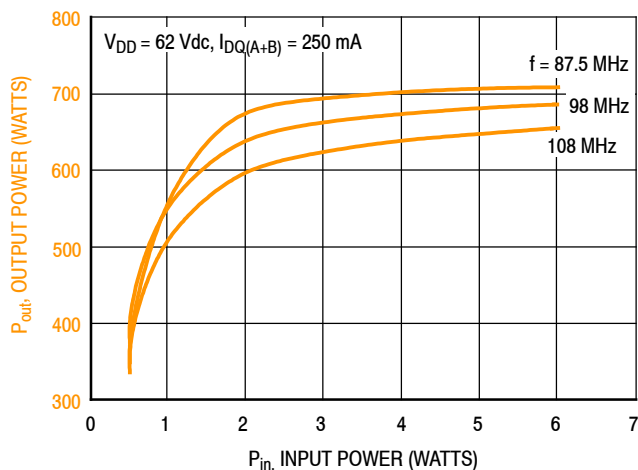
Part	Description	Part Number	Manufacturer
B1	Long Ferrite Bead	2743021447	Fair-Rite
C1	30 pF Chip Capacitor	ATC100B300JT500XT	ATC
C2, C5, C6, C9, C10, C11, C12, C13, C14	1000 pF Chip Capacitor	ATC100B102JT50XT	ATC
C3, C4	10,000 pF Chip Capacitor	ATC200B103KT50XT	ATC
C7, C8	470 pF Chip Capacitor	ATC100B471JT200XT	ATC
C15	1.0 pF Chip Capacitor	ATC100B1R0BT500XT	ATC
C16	470 $\mu$ F, 63 V Electrolytic Capacitor	MCGPR63V477M13X26	Multicomp
C17, C18	10 $\mu$ F Chip Capacitor	C5750X7S2A106M	TDK
C19	470 nF Chip Capacitor	GRM31MR72A474KA35L	Murata
C20	47 nF Chip Capacitor	GRM31MR72A473KA01L	Murata
C21	15 nF Chip Capacitor	C3225CH2A153JT	TDK
Coax1,2	35 $\Omega$ Flex Cable, 4.5" Shield Length	HSF-141C-35	Hongsen Cable
Coax3	50 $\Omega$ Flex Cable, 6.3" Shield Length	SM141	Huber + Suhner
L1	100 nH Inductor	1812SMS-R10JLC	Coilcraft
L2, L3	8.0 nH, 3 Turn Inductor	A03TJLC	Coilcraft
L4	5 Turn, #16 AWG, ID = 0.315" Inductor	Handwound	NXP
Q1	RF Power LD MOS Transistor	MRFX600H	NXP
R1	10 $\Omega$ , 1/4 W Chip Resistor	CRCW120610R0JNEA	Vishay
R2, R3	33 $\Omega$ , 2 W Chip Resistor	352133RFT	TE Connectivity
T1	2–300 MHz, 3 Turns, 9:1 Impedance Ratio Transformer	TUI-LF-9	Communication Concepts
PCB	Rogers RO4350B, 0.030", $\epsilon_r = 3.66$	D111952	MTL

MRFX600H MRFX600HS MRFX600GS

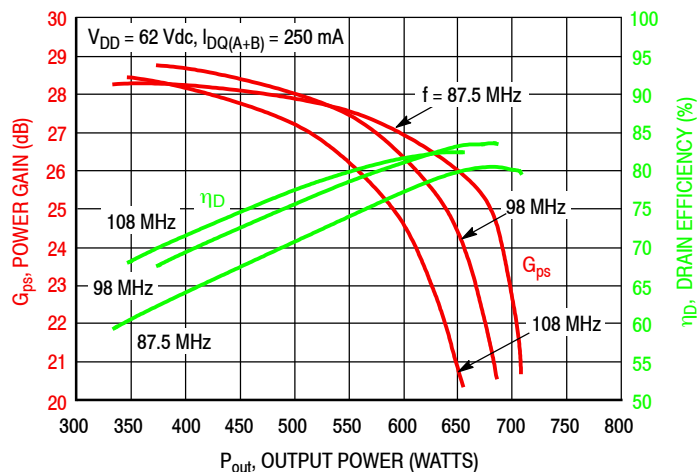
## TYPICAL CHARACTERISTICS – 87.5–108 MHz BROADBAND REFERENCE CIRCUIT



**Figure 5. Power Gain, Drain Efficiency and CW Output Power versus Frequency at a Constant Input Power**



**Figure 6. CW Output Power versus Input Power and Frequency**



**Figure 7. Power Gain and Drain Efficiency versus CW Output Power and Frequency**

## 87.5–108 MHz BROADBAND REFERENCE CIRCUIT

f MHz	Z <sub>source</sub> Ω	Z <sub>load</sub> Ω
87.5	5.46 + j12.00	11.09 + j8.82
98	6.45 + j11.40	11.51 + j8.88
108	5.57 + j11.13	11.84 + j9.06

Z<sub>source</sub> = Test circuit impedance as measured from gate to gate, balanced configuration.

Z<sub>load</sub> = Test circuit impedance as measured from drain to drain, balanced configuration.

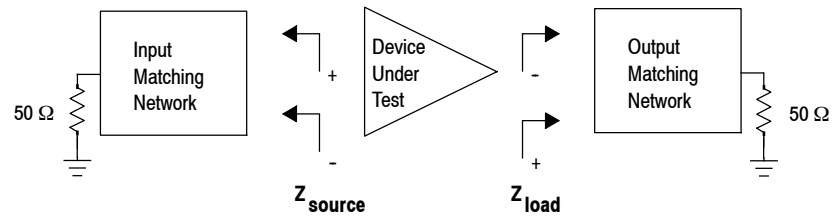
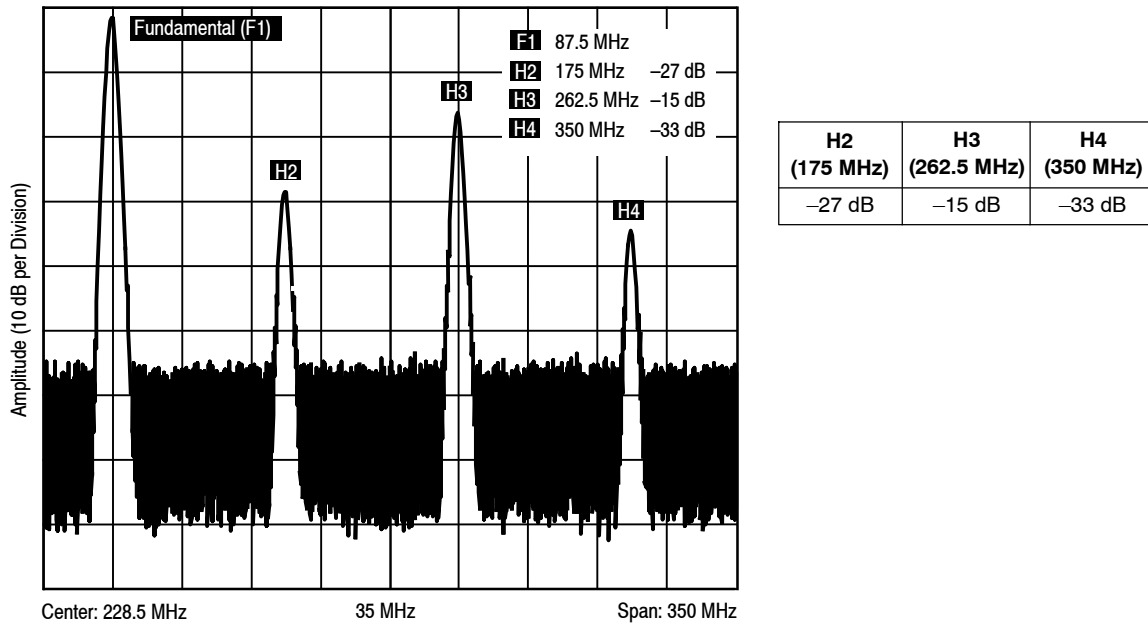


Figure 8. Broadband Series Equivalent Source and Load Impedance – 87.5–108 MHz



**HARMONIC MEASUREMENTS — 87.5–108 MHz  
BROADBAND REFERENCE CIRCUIT**



**Figure 9. 87.5 MHz Harmonics @ 675 W CW**

230 MHz PRODUCTION TEST FIXTURE — 4.0" x 6.0" (10.2 cm x 12.7 cm)

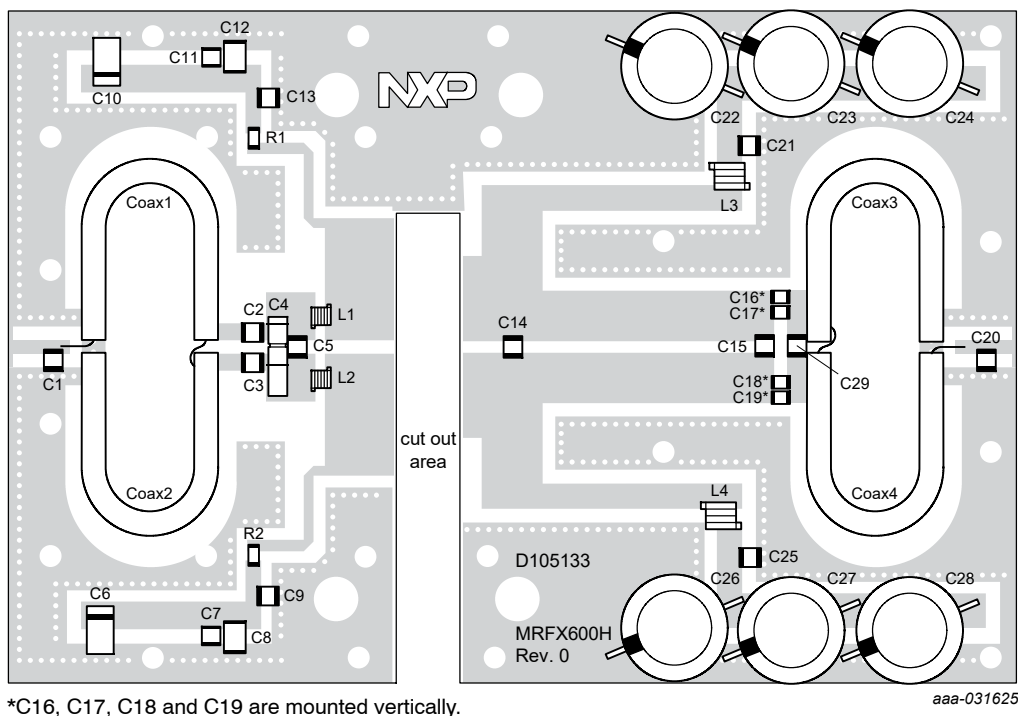


Figure 10. MRFX600H Production Test Fixture Component Layout — 230 MHz

Table 9. MRFX600H Production Test Fixture Component Designations and Values — 230 MHz

Part	Description	Part Number	Manufacturer
C1	13 pF Chip Capacitor	ATC100B130JT500XT	ATC
C2, C3	27 pF Chip Capacitor	ATC100B270JT500XT	ATC
C4	0.8–8.0 pF Variable Capacitor	27291SL	Johanson Components
C5	33 pF Chip Capacitor	ATC100B330JT500XT	ATC
C6, C10	22 $\mu$ F, 35 V Tantalum Capacitor	T491X226K035AT	Kemet
C7, C11	0.1 $\mu$ F Chip Capacitor	CDR33BX104AKWS	AVX
C8, C12	220 nF Chip Capacitor	C1812C224K5RACTU	Kemet
C9, C13, C21, C25	1000 pF Chip Capacitor	ATC100B102JT50XT	ATC
C14, C29	39 pF Chip Capacitor	ATC100B390JT500XT	ATC
C15	43 pF Chip Capacitor	ATC100B430JT500XT	ATC
C16, C17, C18, C19	240 pF Chip Capacitor	ATC100B241JT200XT	ATC
C20	9.1 pF Chip Capacitor	ATC100B9R1BT500XT	ATC
C22, C23, C24, C26, C27, C28	470 $\mu$ F, 100 V Electrolytic Capacitor	MCGPR100V477M16X32	Multicomp
Coax1, 2, 3, 4	25 $\Omega$ Semi-rigid Coax, 2.2" Shield Length	UT-141C-25	Micro-Coax
L1, L2	5 nH Inductor	A02TKLC	Coilcraft
L3, L4	6.6 nH Inductor	GA3093-ALC	Coilcraft
R1, R2	10 $\Omega$ , 1/4 W Chip Resistor	CRCW120610R0JNEA	Vishay
PCB	Rogers AD255C, 0.030", $\epsilon_r = 2.55$ , 1 oz. Copper	D105133	MTL

TYPICAL CHARACTERISTICS — 230 MHz,  $T_C = 25^\circ\text{C}$   
PRODUCTION TEST FIXTURE

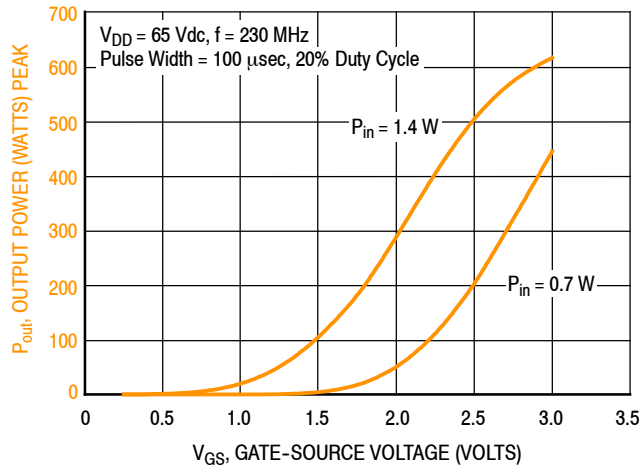
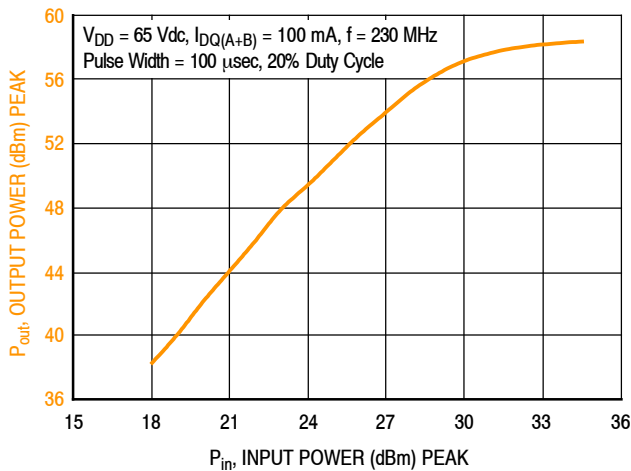


Figure 11. Output Power versus Gate-Source Voltage at a Constant Input Power



f (MHz)	P1dB (W)	P3dB (W)
230	610	677

Figure 12. Output Power versus Input Power

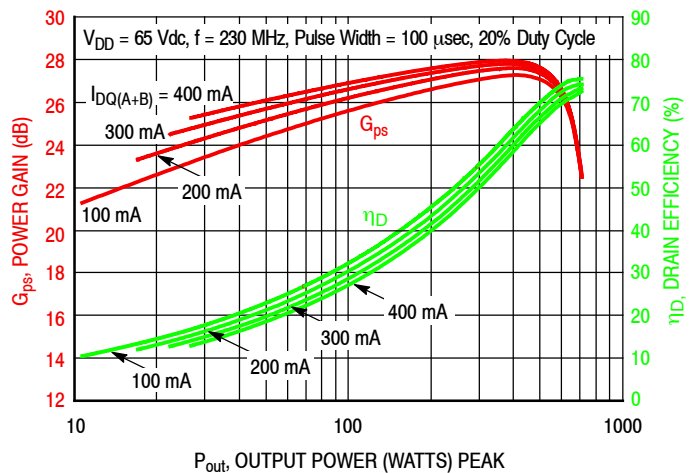


Figure 13. Power Gain and Drain Efficiency versus Output Power and Quiescent Current

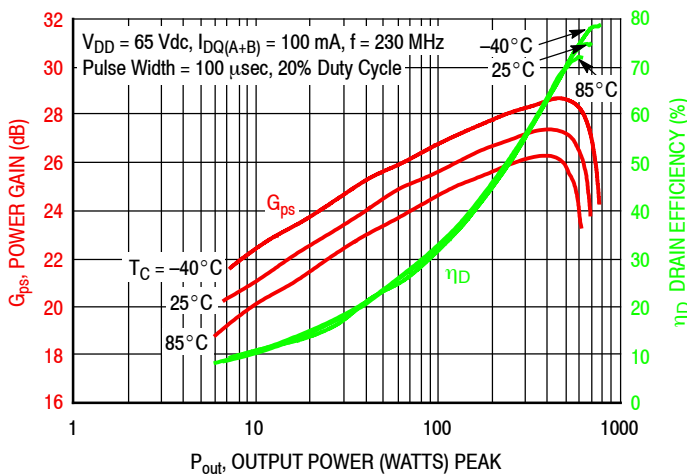


Figure 14. Power Gain and Drain Efficiency versus Output Power

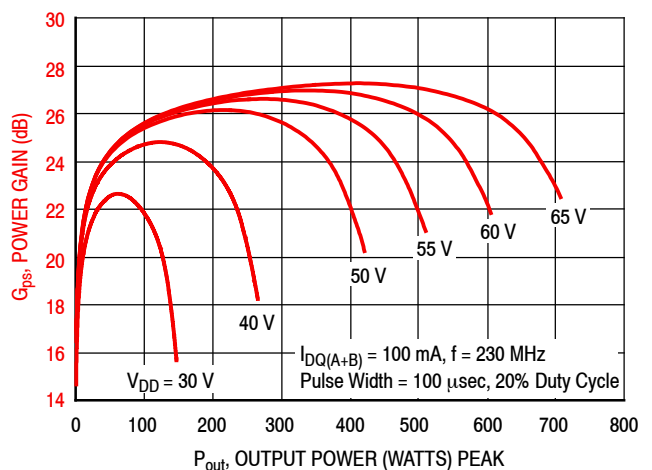


Figure 15. Power Gain versus Output Power and Drain-Source Voltage

MRFX600H MRFX600HS MRFX600GS

## 230 MHz PRODUCTION TEST FIXTURE

f MHz	Z <sub>source</sub> Ω	Z <sub>load</sub> Ω
230	1.5 + j4.9	5.0 + j7.1

Z<sub>source</sub> = Test fixture impedance as measured from gate to gate, balanced configuration.

Z<sub>load</sub> = Test fixture impedance as measured from drain to drain, balanced configuration.

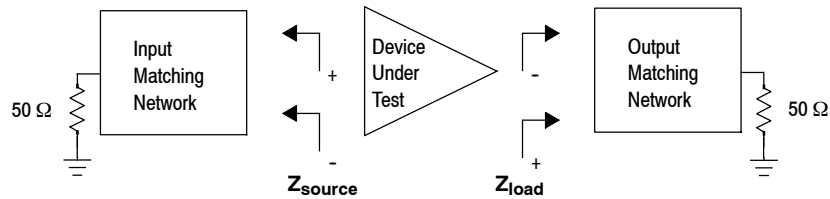


Figure 16. Series Equivalent Source and Load Impedance – 230 MHz



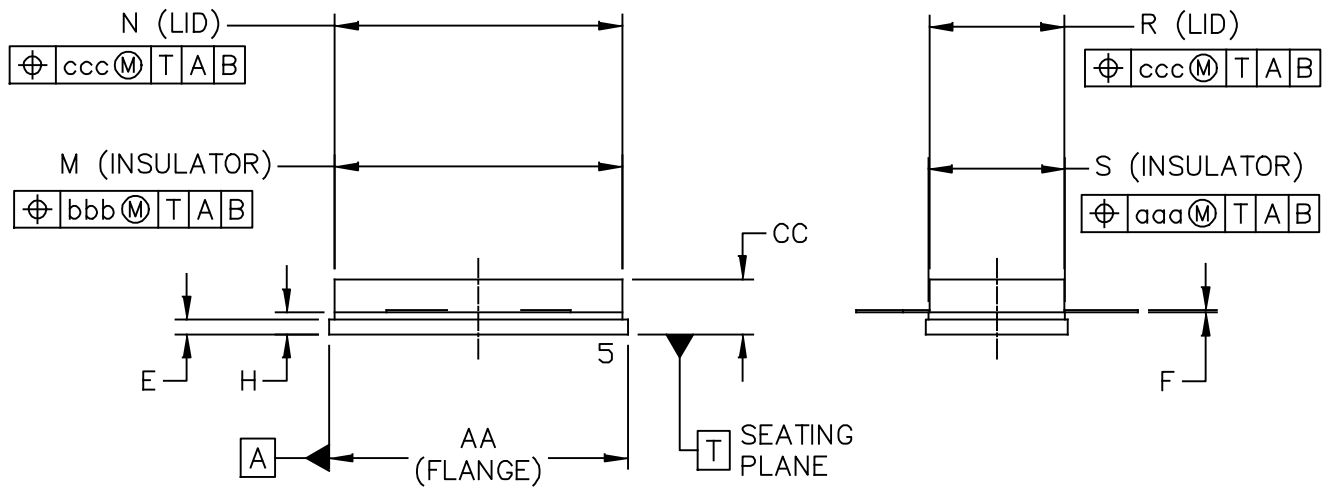
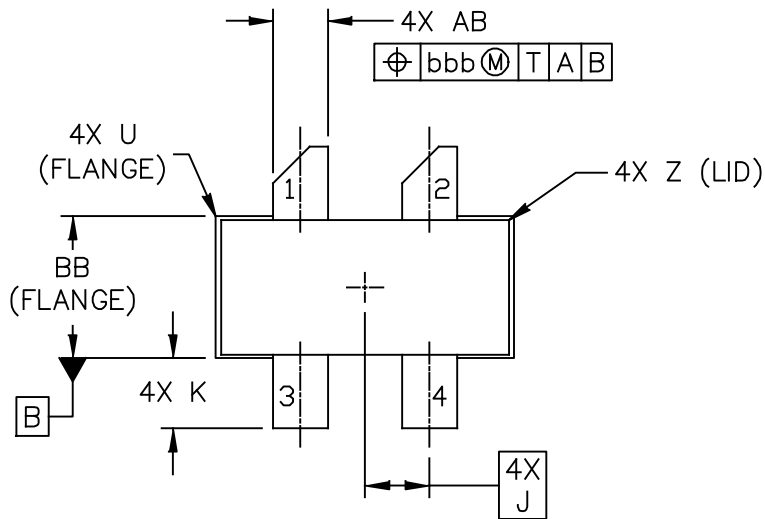
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION H IS MEASURED .030 (0.762) AWAY FROM PACKAGE BODY.

STYLE 1:

- PIN 1. DRAIN  
 2. DRAIN  
 3. GATE  
 4. GATE  
 5. SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16	R	.365	.375	9.27	9.53
B	.380	.390	9.65	9.91	S	.365	.375	9.27	9.52
C	.125	.170	3.18	4.32	U		.040		1.02
E	.035	.045	0.89	1.14	Z		.030		0.76
F	.003	.006	0.08	0.15	AB	.145	.155	3.68	3.94
G	1.100 BSC		27.94 BSC						
H	.057	.067	1.45	1.7	aaa		.005		0.127
J	.175 BSC		4.44 BSC		bbb		.010		0.254
K	.170	.210	4.32	5.33	ccc		.015		0.381
M	.774	.786	19.61	20.02					
N	.772	.788	19.61	20.02					
Q	ø.118	ø.138	ø3	ø3.51					
© NXP SEMICONDUCTORS N. V. ALL RIGHTS RESERVED			MECHANICAL OUTLINE			PRINT VERSION NOT TO SCALE			
TITLE:  NI 780-4					DOCUMENT NO: 98ASA10793D		REV: A		
					STANDARD: NON-JEDEC				
					SOT1827-1			17 MAR 2016	



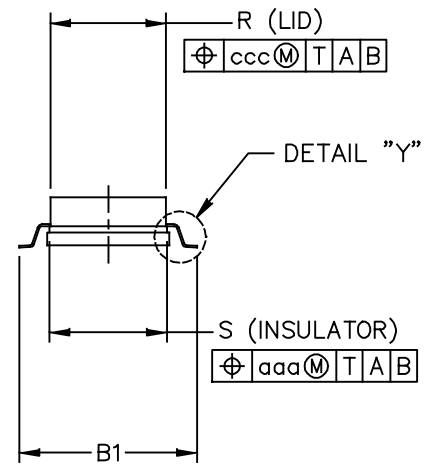
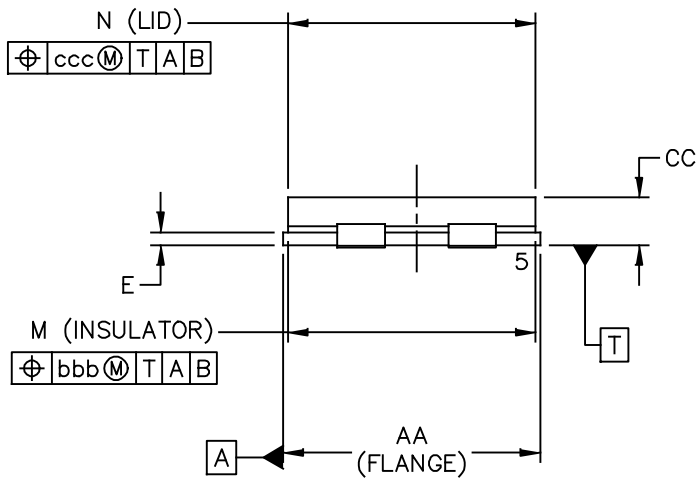
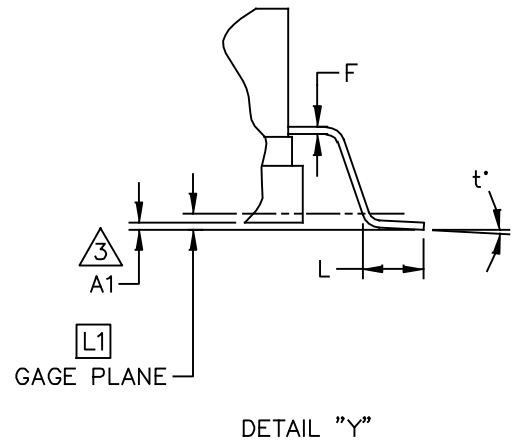
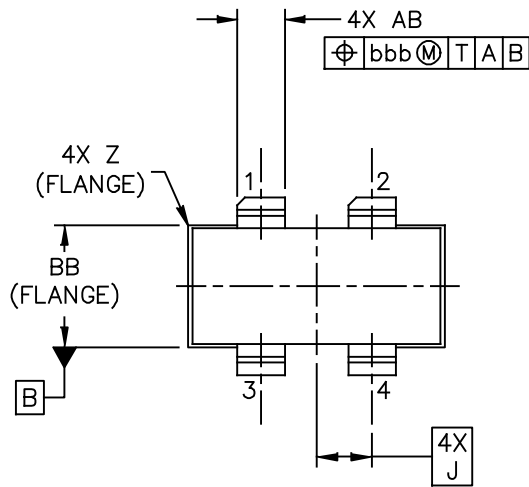
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TITLE:  NI-780S-4L	DOCUMENT NO: 98ASA10718D STANDARD: NON-JEDEC SOT1826-1	REV: C  01 AUG 2016

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED .030 (0.762) AWAY FROM FLANGE TO CLEAR EPOXY FLOW OUT PARALLEL TO DATUM B.

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
AA	.805	.815	20.45	20.70	U		.040		1.02
BB	.382	.388	9.70	9.86	Z		.030		0.76
CC	.125	.170	3.18	4.32	AB	.145	.155	3.68	- 3.94
E	.035	.045	0.89	1.14					
F	.003	.006	0.08	0.15	aaa		.005		0.127
H	.057	.067	1.45	1.70	bbb		.010		0.254
J	.175 BSC		4.44 BSC		ccc		.015		0.381
K	.170	.210	4.32	5.33					
M	.774	.786	19.61	20.02					
N	.772	.788	19.61	20.02					
R	.365	.375	9.27	9.53					
S	.365	.375	9.27	9.52					
© NXP SEMICONDUCTORS N. V. ALL RIGHTS RESERVED			MECHANICAL OUTLINE			PRINT VERSION NOT TO SCALE			
TITLE:  NI-780S-4L					DOCUMENT NO: 98ASA10718D      REV: C				
					STANDARD: NON-JEDEC				
					SOT1826-1			01 AUG 2016	





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TITLE:  NI-780GS-4L	DOCUMENT NO: 98ASA00238D	REV: C
	STANDARD: NON-JEDEC	
	SOT1805-1	23 FEB 2016

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.

2. CONTROLLING DIMENSION: INCH.

3. DIMENSION A1 IS MEASURED WITH REFERENCE TO DATUM T. THE POSITIVE VALUE IMPLIES THAT THE PACKAGE BOTTOM IS HIGHER THAN THE LEAD BOTTOM.

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
AA	.805	.815	20.45	20.70	Z	R.000	R.040	R0.00	R1.02
A1	.002	.008	0.05	0.20	AB	.145	.155	3.68	3.94
BB	.380	.390	9.65	9.91	t°	0°	8°	0°	8°
B1	.546	.562	13.87	14.27	aaa	.005		0.13	
CC	.125	.170	3.18	4.32	bbb	.010		0.25	
E	.035	.045	0.89	1.14	ccc	.015		0.38	
F	.003	.006	0.08	0.15					
L	.038	.046	0.97	1.17					
L1	.010 BSC		0.25 BSC						
J	.175 BSC		4.44 BSC						
M	.774	.786	19.66	19.96					
N	.772	.788	19.61	20.02					
R	.365	.375	9.27	9.53					
S	.365	.375	9.27	9.53					
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TITLE:  NI-780GS-4L					DOCUMENT NO: 98ASA00238D      REV: C				
					STANDARD: NON-JEDEC				
					SOT1805-1			23 FEB 2016	

## PRODUCT DOCUMENTATION, SOFTWARE AND TOOLS

Refer to the following resources to aid your design process.

### Application Notes

- AN1908: Solder Reflow Attach Method for High Power RF Devices in Air Cavity Packages
- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

### Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

### Software

- Electromigration MTTF Calculator
- RF High Power Model
- .s2p File

### Development Tools

- Printed Circuit Boards

### To Download Resources Specific to a Given Part Number:

1. Go to <http://www.nxp.com/RF>
2. Search by part number
3. Click part number link
4. Choose the desired resource from the drop down menu

## REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Sept. 2018	<ul style="list-style-type: none"><li>• Initial release of data sheet</li></ul>

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